In the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A thin-film capacitor element comprising:

an insulative substrate having a via hole filled with a conductive material;

a lower electrode;

a dielectric layer; and

an upper electrode~~,~~;

wherein the lower electrode, the dielectric layer, and the upper electrode are successively deposited in order on the insulative substrate,~~wherein~~ either one of the lower electrode and the upper electrode connects to an end face of the conductive material~~,~~; and the dielectric layer is shaped like a ring to surround the via hole.

2. (Previously presented) A thin-film capacitor element according to Claim 1, wherein the dielectric layer is shaped like a ring with the via hole as a center.

3. (Original) A thin-film capacitor element according to Claim 1, wherein the insulative substrate is made of low-temperature-sintered ceramic.

4. (New) A thin-film capacitor element comprising:

an insulative substrate having a via hole filled with a conductive material;

a lower electrode;

a dielectric layer; and

an upper electrode; wherein the lower electrode, the dielectric layer, and the upper electrode are successively deposited in order on the insulative substrate,

wherein the dielectric layer does not cover an end face of the via hole,

either one of the lower electrode and the upper electrode connects to an end face of the conductive material in an area not having a dielectric layer; and

the dielectric layer is shaped like a ring to surround the via hole.

5. (New) A thin-film capacitor element according to Claim 4, wherein an area between the dielectric layer and the via hole is ring shaped.

6. (New) A thin-film capacitor element according to Claim 4, wherein the insulative substrate is made of low-temperature-sintered ceramic.